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- Low Power Consumption
- Wide Common-Mode and Differential Voltage Ranges
- Low Input Bias and Offset Currents
- Output Short-Circuit Protection
- Low Total Harmonic Distortion 0.003% Typ

- Low Noise
 - $V_n = 18 \text{ nV}/\sqrt{\text{Hz}}$ Typ at f = 1 kHz
- High Input Impedance . . . JFET Input Stage
- Internal Frequency Compensation
- Latch-Up-Free Operation
- High Slew Rate . . . 13 V/μs Typ
- Common-Mode Input Voltage Range Includes V_{CC+}

description

The JFET-input operational amplifiers in the TL07_ series are designed as low-noise versions of the TL08_ series amplifiers with low input bias and offset currents and fast slew rate. The low harmonic distortion and low noise make the TL07_ series ideally suited for high-fidelity and audio preamplifier applications. Each amplifier features JFET inputs (for high input impedance) coupled with bipolar output stages integrated on a single monolithic chip.

The C-suffix devices are characterized for operation from 0° C to 70° C. The I-suffix devices are characterized for operation from -40° C to 85° C. The M-suffix devices are characterized for operation over the full military temperature range of -55° C to 125° C.

AVAILABLE OPTIONS

| | | | | | PA | CKAGE | | | |
|-------------------|--------------------------------|---------------------------------|----------------------------------|-----------------------|---------------------------|---------------------------------|---------------------------------|--------------------------|------------------------|
| TA | V _{IO} max AT 25°C | SMALL OUTLINE (D)† | CHIP CARRIER (FK) | CERAMIC DIP (J) | CERAMIC DIP (JG) | PLASTIC DIP (N) | PLASTIC DIP (P) | TSSOP PACKAGE (PW) | FLAT PACKAGE (W) |
| | 10 mV 6 mV 3 mV | TL071CD TL071ACD TL071BCD | _ | _ | ı | _ | TL071CP TL071ACP TL071BCP | TL071CPWLE — — | _ |
| 0°C to 70°C | 10 mV 6 mV 3 mV | TL072CD TL072ACD TL072BCD | _ | _ | _ | _ | TL072CP TL072ACP TL072BCP | TL072CPWLE — — | _ |
| | 10 mV 6 mV 3 mV | TL074CD TL074ACD TL074BCD | _ | | ı | TL074CN TL074ACN TL074BCN | _ | TL074CPWLE — — | _ |
| -40°C to 85°C | 6 mV | TL071ID TL072ID TL074ID | | 1 | ı | — — TL074IN | TL071IP TL072IP — | ı | _ |
| -55°C to 125°C | 6 mV 6 mV 9 mV | _ | TL071MFK TL072MFK TL074MFK | — — TL074MJ | TL071MJG TL072MJG — | _ TL074MN | — TL072MP — | | — — TL074MW |

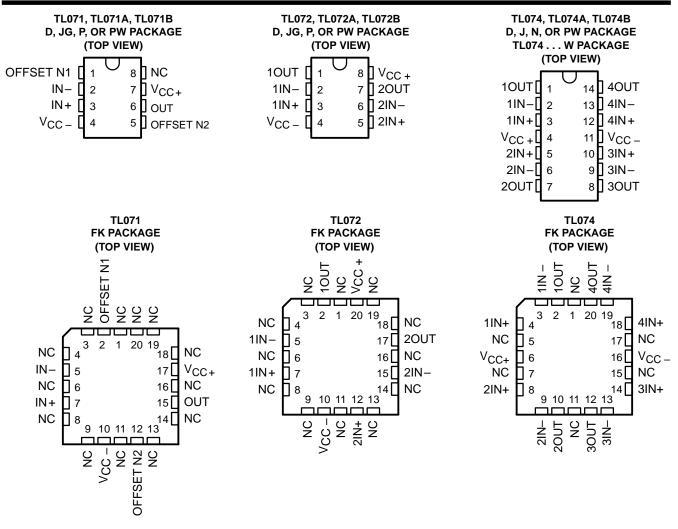
[†] The D package is available taped and reeled. Add the suffix R to the device type (e.g., TL071CDR). The PW package is only available left-ended taped and reeled (e.g., TL072CPWLE).



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



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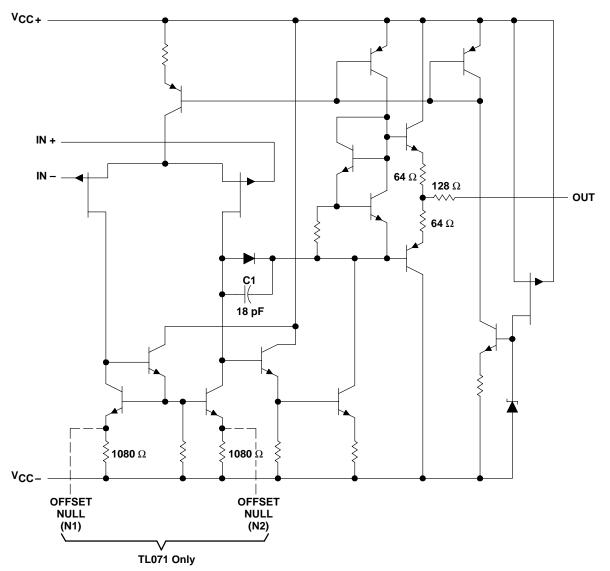
NC - No internal connection

symbols





schematic (each amplifier)



All component values shown are nominal.

| COMPONENT COUNT [†] | | | | | | | | | |
|------------------------------|-------|-------|-------|--|--|--|--|--|--|
| COMPONENT TYPE | TL071 | TL072 | TL074 | | | | | | |
| Resistors | 11 | 22 | 44 | | | | | | |
| Transistors | 14 | 28 | 56 | | | | | | |
| JFET | 2 | 4 | 6 | | | | | | |
| Diodes | 1 | 2 | 4 | | | | | | |
| Capacitors | 1 | 2 | 4 | | | | | | |
| epi-FET | 1 | 2 | 4 | | | | | | |

[†] Includes bias and trim circuitry



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

| Supply voltage, V _{CC+} (see Note 1) |
|--|
| Supply voltage, V _{CC} (see Note 1) |
| Differential input voltage, V _{ID} (see Note 2)±30 V |
| Input voltage, V _I (see Notes 1 and 3)±15 V |
| Duration of output short circuit (see Note 4) unlimited |
| Continuous total power dissipation See Dissipation Rating Table |
| Operating free-air temperature range, T _A : C suffix |
| I suffix –40°C to 85°C |
| M suffix−55°C to 125°C |
| Storage temperature range65°C to 150°C |
| Case temperature for 60 seconds: FK package 260°C |
| Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: J, JG, or W package 300°C |
| Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: D, N, P, or PW package 260°C |

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to the midpoint between VCC+ and VCC-.
 - 2. Differential voltages are at IN+ with respect to IN-.
 - 3. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 V, whichever is less.
 - 4. The output may be shorted to ground or to either supply. Temperature and/or supply voltages must be limited to ensure that the dissipation rating is not exceeded.

DISSIPATION RATING TABLE

| PACKAGE | $T_{\mbox{\scriptsize A}} \le 25^{\circ}\mbox{\scriptsize C}$ POWER RATING | DERATING FACTOR | DERATE ABOVE T _A | T _A = 70°C POWER RATING | T _A = 85°C POWER RATING | T _A = 125°C POWER RATING |
|-------------|--|--------------------|--------------------------------|---------------------------------------|---------------------------------------|--|
| D (8 pin) | 680 mW | 5.8 mW/°C | 33°C | 465 mW | 378 mW | N/A |
| D (14 pin) | 680 mW | 7.6 mW/°C | 60°C | 604 mW | 490 mW | N/A |
| FK | 680 mW | 11.0 mW/°C | 88°C | 680 mW | 680 mW | 273 mW |
| J | 680 mW | 11.0 mW/°C | 88°C | 680 mW | 680 mW | 273 mW |
| JG | 680 mW | 8.4 mW/°C | 69°C | 672 mW | 546 mW | 210 mW |
| N | 680 mW | 9.2 mW/°C | 76°C | 680 mW | 597 mW | N/A |
| Р | 680 mW | 8.0 mW/°C | 65°C | 640 mW | 520 mW | N/A |
| PW (8 pin) | 525 mW | 4.2 mW/°C | 70°C | 525 mW | N/A | N/A |
| PW (14 pin) | 700 mW | 5.6 mW/°C | 70°C | 700 mW | N/A | N/A |
| W | 680 mW | 8.0 mW/°C | 65°C | 640 mW | 520 mW | 200 mW |



electrical characteristics, $V_{CC\pm} = \pm 15 \text{ V}$ (unless otherwise noted)

| P/ | ARAMETER | TEST CON | IDITIONS† | T _A ‡ | | TL071C TL072C TL074C | | 7 | L071A0 L072A0 L074A0 | ; | 1 | L071BC L072BC L074BC | ; | | TL071I TL072I TL074I | | UNIT |
|----------------------------------|---|-------------------------------------|---|------------------|-----|----------------------------|-----|-----|----------------------------|-----|-----|----------------------------|-----|-----|----------------------------|-----|-------|
| | | | - | | MIN | TYP | MAX | |
| VIO | Input offset voltage | $V_{O} = 0$, | $R_S = 50 \Omega$ | 25°C | | 3 | 10 | | 3 | 6 | | 2 | 3 | | 3 | 6 | mV |
| 10 | | , | | Full range | | | 13 | | | 7.5 | | | 5 | | | 8 | |
| αVIO | Temperature coefficient of input offset voltage | V _O = 0, | R _S = 50 Ω | Full range | | 18 | | | 18 | | | 18 | | | 18 | | μV/°C |
| I _{IO} | Input offset current | V _O = 0 | | 25°C | | 5 | 100 | | 5 | 100 | | 5 | 100 | | 5 | 100 | рА |
| .10 | input onset current | VO = V | | Full range | | | 10 | | | 2 | | - | 2 | | - | 2 | nA |
| I _{IB} | Input bias current§ | V _O = 0 | | 25°C | | 65 | 200 | | 65 | 200 | | 65 | 200 | | 65 | 200 | pА |
| <u> </u> | | <u> </u> | | Full range | | | 7 | | | 7 | | | 7 | | | 20 | nA |
| VICR | Common-mode input voltage range | | | 25°C | ±11 | –12 to 15 | | ±11 | –12 to 15 | | ±11 | –12 to 15 | | ±11 | -12 to 15 | | ٧ |
| | Maximum peak | R _L = 10 kΩ | | 25°C | ±12 | ±13.5 | | ±12 | ±13.5 | | ±12 | ±13.5 | | ±12 | ±13.5 | | |
| V _{OM} | output voltage | $R_L \ge 10 \text{ k}\Omega$ | | Full rongs | ±12 | | | ±12 | | | ±12 | | | ±12 | | | V |
| | swing | $R_L \ge 2 k\Omega$ | | Full range | ±10 | | | ±10 | | | ±10 | | | ±10 | | | |
| | Large-signal | ., .,,,, | | 25°C | 25 | 200 | | 50 | 200 | | 50 | 200 | | 50 | 200 | | |
| AVD | differential voltage amplification | $V_0 = \pm 10 \text{ V},$ | R _L ≥ 2 kΩ | Full range | 15 | | | 25 | | | 25 | | | 25 | | | V/mV |
| B ₁ | Unity-gain bandwidth | | | 25°C | | 3 | | | 3 | | | 3 | | | 3 | | MHz |
| rį | Input resistance | | | 25°C | | 1012 | | | 10 ¹² | | | 10 ¹² | | | 10 ¹² | | Ω |
| CMRR | Common-mode rejection ratio | $V_{IC} = V_{ICR}$ $V_{O} = 0$, | nin, R _S = 50 Ω | 25°C | 70 | 100 | | 75 | 100 | | 75 | 100 | | 75 | 100 | | dB |
| kSVR | Supply-voltage rejection ratio $(\Delta V_{CC\pm}/\Delta V_{IO})$ | $V_{CC} = \pm 9 V$ $V_{O} = 0$, | to $\pm 15 \text{ V}$, R _S = 50Ω | 25°C | 70 | 100 | | 80 | 100 | | 80 | 100 | | 80 | 100 | | dB |
| Icc | Supply current (each amplifier) | V _O = 0, | No load | 25°C | | 1.4 | 2.5 | | 1.4 | 2.5 | | 1.4 | 2.5 | | 1.4 | 2.5 | mA |
| V _{O1} /V _{O2} | Crosstalk attenuation | A _{VD} = 100 | | 25°C | | 120 | | | 120 | | | 120 | | | 120 | | dB |
| _ | | • | | • | | | | | | | | | | | | | |

[†] All characteristics are measured under open-loop conditions with zero common-mode voltage unless otherwise specified.

‡ Full range is T_A = 0°C to 70°C for TL07_C, TL07_AC, TL07_BC and is T_A = -40°C to 85°C for TL07_I.

§ Input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive as shown in Figure 4. Pulse techniques must be used that maintain the junction temperature as close to the ambient temperature as possible.

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electrical characteristics, $V_{CC\pm} = \pm 15 \text{ V}$ (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS† | | T _A ‡ | TL071M TL072M | | | , | TL074M | | UNIT |
|----------------------------------|---|-------------------------------------|--|------------------|------------------|----------|-----|-----|----------|-----|----------------|
| | | | | | MIN | TYP | MAX | MIN | TYP | MAX | |
| VIO | Input offset voltage | V _O = 0, | $R_S = 50 \Omega$ | 25°C | | 3 | 6 | | 3 | 9 | mV |
| ۷IO | input onset voitage | VO = 0, | NS = 50 22 | Full range | | | 9 | | | 15 | IIIV |
| αγιο | Temperature coefficient of input offset voltage | V _O = 0, | $R_S = 50 \Omega$ | Full range | | 18 | | | 18 | | μV/°C |
| lio | Input offset current | V _O = 0 | | 25°C | | 5 | 100 | | 5 | 100 | pA |
| 10 | input onset current | vO = 0 | | Full range | | | 20 | | | 20 | nA |
| IB | Input bias current‡ | V _O = 0 | | 25°C | | 65 | 200 | | 65 | 200 | pA |
| 'IB | input bias current+ | VO = 0 | | | | | 50 | | | 50 | nA |
| | Common-mode input | | | | | -12 | | | -12 | | |
| VICR | voltage range | | | 25°C | ±11 | to 15 | | ±11 | to 15 | | V |
| | | R _L = 10 kΩ | | 25°C | ±12 | ±13.5 | | ±12 | | | |
| VOM | Maximum peak output | $R_{L} = 10 \text{ k}\Omega$ | | 25 0 | ±12 | ±10.0 | | ±12 | ±13.5 | | - _V |
| VOM | voltage swing | $R_1 \ge 2 k\Omega$ | | Full range | ±10 | | | ±10 | | | ı v |
| | l anno airmal differential | 11 2 2 1/32 | | 25°C | 35 | 200 | | 35 | 200 | | |
| AVD | Large-signal differential voltage amplification | $V_0 = \pm 10 \text{ V},$ | $R_L \ge 2 k\Omega$ | 25 0 | 15 | 200 | | 15 | | | V/mV |
| B ₁ | Unity-gain bandwidth | T _A = 25°C | | | | 3 | | | 3 | | MHz |
| rį | Input resistance | T _A = 25°C | | | | 1012 | | | 1012 | | Ω |
| CMRR | Common-mode rejection ratio | $V_{IC} = V_{ICR}$ $V_{O} = 0$, | | 25°C | 80 | 86 | | 80 | 86 | | dB |
| kSVR | Supply-voltage rejection ratio ($\Delta V_{CC\pm}/\Delta V_{IO}$) | $V_{CC} = \pm 9 V$ $V_{O} = 0$, | to ± 15 V, R _S = 50 Ω | 25°C | 80 | 86 | | 80 | 86 | | dB |
| Icc | Supply current (each amplifier) | V _O = 0, | No load | 25°C | | 1.4 | 2.5 | | 1.4 | 2.5 | mA |
| V _{O1} /V _{O2} | Crosstalk attenuation | $A_{VD} = 100$ | | 25°C | | 120 | | | 120 | | dB |

[†] Input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive as shown in Figure 4. Pulse techniques must be used that will maintain the junction temperature as close to the ambient temperature as possible.



[‡] All characteristics are measured under open-loop conditions with zero common-mode voltage unless otherwise specified. Full range is $T_A = -55^{\circ}C$ to $125^{\circ}C$.

operating characteristics, $V_{CC\pm}\,{=}\,\pm15$ V, $T_A\,{=}\,25^{\circ}C$

| PARAMETER | | TEST CO | 7 | ΓL07xM | | ALL | UNIT | | | |
|----------------|--------------------------------|---|---|--------|--------|-----|------|--------|-----|--------------------|
| | | TEST CONDITIONS | | MIN | TYP | MAX | MIN | TYP | MAX | UNIT |
| SR | Slew rate at unity gain | V _I = 10 V, C _L = 100 pF, | $R_L = 2 k\Omega$, See Figure 1 | 5 | 13 | | 8 | 13 | | V/μs |
| | Rise time overshoot | $V_{I} = 20 \text{ mV},$ | $R_L = 2 k\Omega$, | | 0.1 | | | 0.1 | | μs |
| τ _r | factor | C _L = 100 pF, | See Figure 1 | | 20% | | | 20% | | |
| V | Equivalent input noise | Rs = 20 Ω | f = 1 kHz | | 18 | | | 18 | | nV/√ Hz |
| V _n | voltage | KS = 20 12 | f = 10 Hz to 10 kHz | | 4 | | | 4 | | μV |
| In | Equivalent input noise current | $R_S = 20 \Omega$, | f = 1 kHz | | 0.01 | | | 0.01 | | pA/√ Hz |
| THD | Total harmonic distortion | $V_{l} rms = 6 V,$ $R_{L} \ge 2 k\Omega,$ $f = 1 kHz$ | $A_{VD} = 1,$ $R_S \le 1 \text{ k}\Omega,$ | | 0.003% | | (| 0.003% | | |

PARAMETER MEASUREMENT INFORMATION

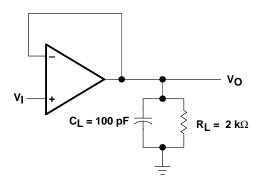


Figure 1. Unity-Gain Amplifier

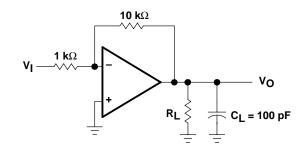


Figure 2. Gain-of-10 Inverting Amplifier

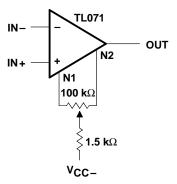


Figure 3. Input Offset Voltage Null Circuit

TL071, TL071A, TL071B, TL072 TL072A, TL072B, TL074, TL074A, TL074B LOW-NOISE JFET-INPUT OPERATIONAL AMPLIFIERS SLOS080D - SEPTEMBER 1978 - REVISED AUGUST 1996

TYPICAL CHARACTERISTICS

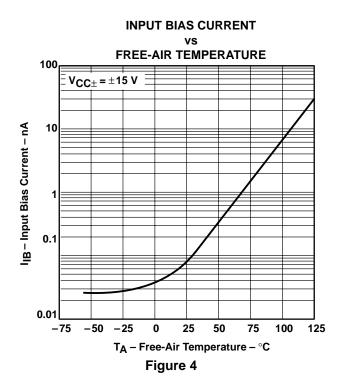
Table of Graphs

| | | | FIGURE |
|-----------------|---|--|-------------------------|
| l _{IB} | Input bias current | vs Free-air temperature | 4 |
| Vом | Maximum output voltage | vs Frequency vs Free-air temperature vs Load resistance vs Supply voltage | 5, 6, 7 8 9 10 |
| AVD | Large-signal differential voltage amplification | vs Free-air temperature vs Frequency | 11 12 |
| | Phase shift | vs Frequency | 12 |
| | Normalized unity-gain bandwidth | vs Free-air temperature | 13 |
| | Normalized phase shift | vs Free-air temperature | 13 |
| CMRR | Common-mode rejection ratio | vs Free-air temperature | 14 |
| Icc | Supply current | vs Supply voltage vs Free-air temperature | 15 16 |
| P_{D} | Total power dissipation | vs Free-air temperature | 17 |
| | Normalized slew rate | vs Free-air temperature | 18 |
| Vn | Equivalent input noise voltage | vs Frequency | 19 |
| THD | Total harmonic distortion | vs Frequency | 20 |
| | Large-signal pulse response | vs Time | 21 |
| ٧o | Output voltage | vs Elapsed time | 22 |



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TYPICAL CHARACTERISTICS[†]



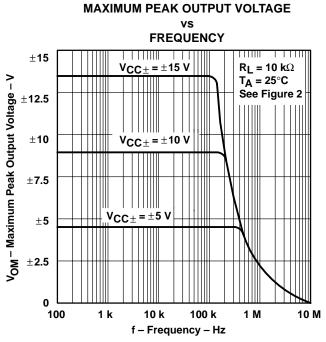


Figure 5

MAXIMUM PEAK OUTPUT VOLTAGE ٧S **FREQUENCY** ±15 $R_L = 2 k\Omega$ V_{OM} - Maximum Peak Output Voltage - V T_A = 25°C $V_{CC\pm} = \pm 15 \text{ V}$ ±12.5 See Figure 2 ± 10 $V_{CC\pm} = \pm 10 \text{ V}$ ±7.5 $\pm \mathbf{5}$ $V_{CC\pm} = \pm 5 V$ ±2.5

10 k

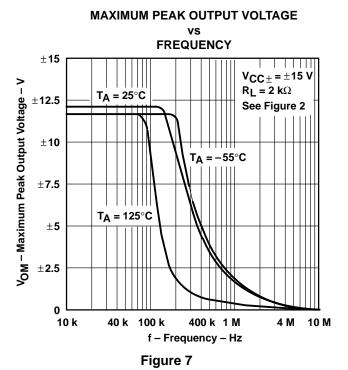
Figure 6

f - Frequency - Hz

100 k

0 └ 100

1 k

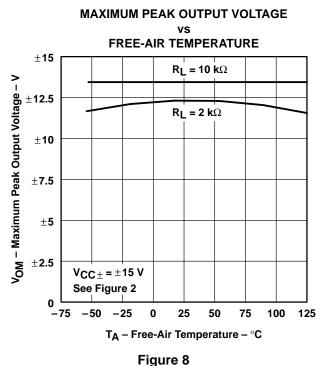


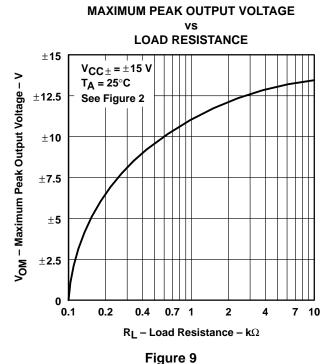
10 M



[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS[†]

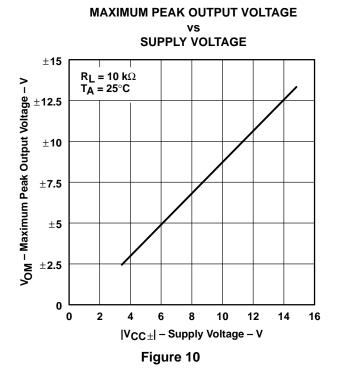


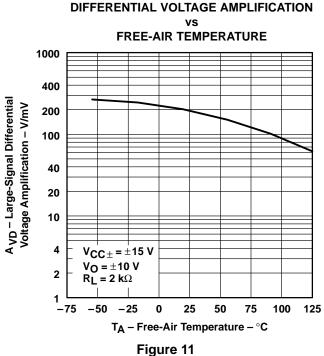


rigure o



LARGE-SIGNAL





[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



TYPICAL CHARACTERISTICS[†]

LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT

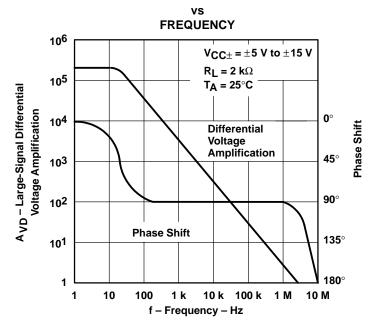


Figure 12

NORMALIZED UNITY-GAIN BANDWIDTH AND PHASE SHIFT

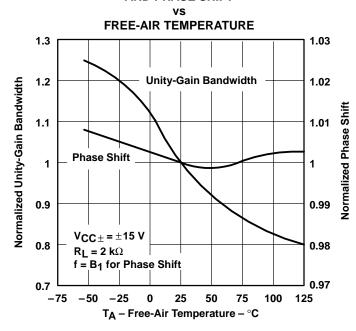


Figure 13

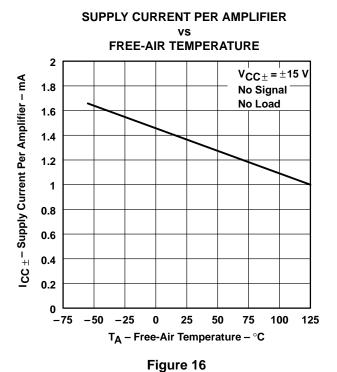
[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



TYPICAL CHARACTERISTICS[†]

COMMON-MODE REJECTION RATIO FREE-AIR TEMPERATURE 89 $V_{CC\pm} = \pm 15 V$ CMRR - Common-Mode Rejection Ratio - dB $R_L = 10 \text{ k}\Omega$ 88 87 86 85 84 83 -50 -25 25 50 75 100 **-75** 125 T_A - Free-Air Temperature - °C

Figure 14



SUPPLY CURRENT PER AMPLIFIER

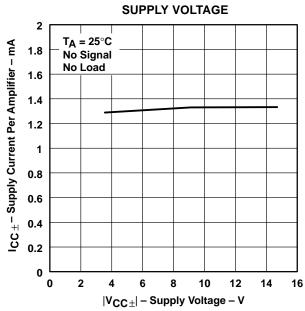


Figure 15

TOTAL POWER DISSIPATION

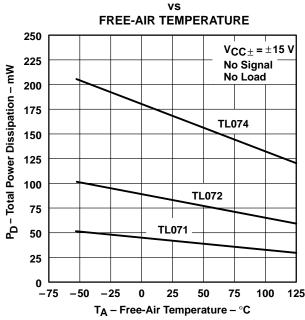


Figure 17

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



TYPICAL CHARACTERISTICS

NORMALIZED SLEW RATE VS FREE-AIR TEMPERATURE 1.15 $V_{CC\pm} = \pm 15 \text{ V}$ $R_L = 2 \text{ k}\Omega$ $C_L = 100 \text{ pF}$ 1.05 10.95 0.90

Normalized Slew Rate – V/µ s

0.85

_75

-50

-25

Figure 18

25

 T_A – Free-Air Temperature – $^{\circ}C$

50

75

125

100

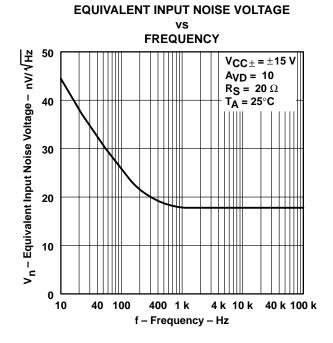


Figure 19

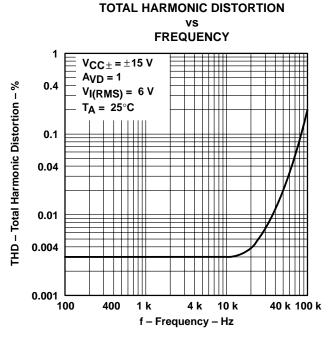
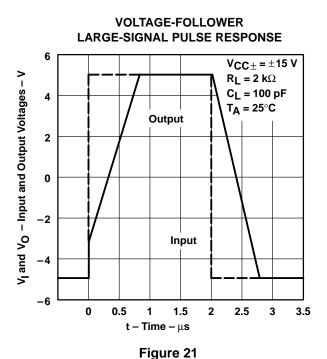


Figure 20



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TYPICAL CHARACTERISTICS

OUTPUT VOLTAGE ELAPSED TIME 28 24 Overshoot V_O - Output Voltage - mV 20 90% 16 12 8 4 10% $V_{CC\pm} = \pm 15 V$ $R_L = 2 k\Omega$ 0 T_A = 25°C 0 0.2 0.3 0.4 0.5 0.6 $\textbf{t-Elapsed Time} - \mu \textbf{s}$

Figure 22



APPLICATION INFORMATION

Table of Application Diagrams

| APPLICATION DIAGRAM | PART NUMBER | FIGURE |
|-------------------------------|----------------|--------|
| 0.5-Hz square-wave oscillator | TL071 | 23 |
| High-Q notch filter | TL071 | 24 |
| Audio-distribution amplifier | TL074 | 25 |
| 100-kHz quadrature oscillator | TL072 | 26 |
| AC amplifier | TL071 | 27 |

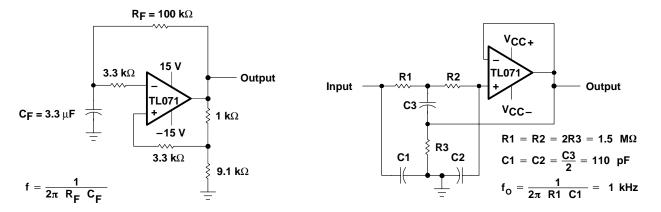


Figure 23. 0.5-Hz Square-Wave Oscillator

Figure 24. High-Q Notch Filter

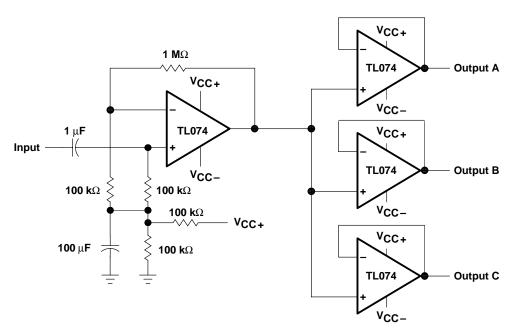
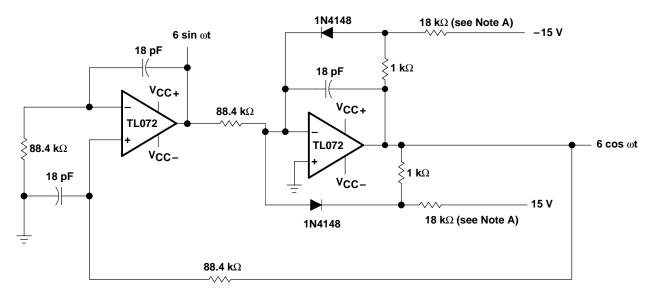


Figure 25. Audio-Distribution Amplifier



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APPLICATION INFORMATION



NOTE A: These resistor values may be adjusted for a symmetrical output.

Figure 26. 100-kHz Quadrature Oscillator

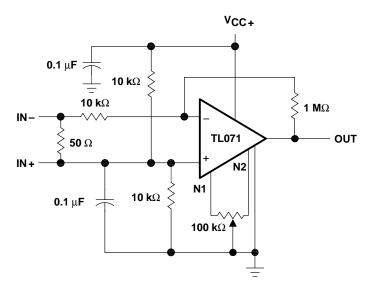


Figure 27. AC Amplifier



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